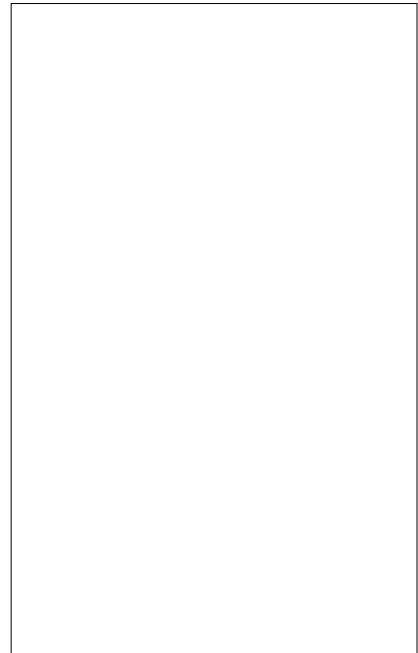


JCT625CH 25A SCR

Rev.A.1.1

## DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT625CH SCR provides high  $dV/dt$  rate with strong resistance to electromagnetic interference. It is especially



Peak gate power	$P_{GM}$	20	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	0.5	kV

## ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12V R_L=33$	-	-	20	mA
$V_{GT}$		-	-	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=150 R_L=3.3k$	0.2	-	-	V
$I_L$	$I_G=1.2I_{GT}$	-	-	70	mA
$I_H$	$I_T=500mA$	-	-	60	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125$	1200	-	-	V/s
	$V_D=400V$ Gate Open $T_j=150$	800	-	-	
$t_{on}$	$I_G=20mA I_A=200mA I_R=20mA$ $T_j=25$	-	2	-	s
$t_{off}$		-	50	-	

## STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=50A t_p=380 s$	$T_j=25$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=150$	0.7	V
$R_D$	Dynamic resistance	$T_j=150$	18	P
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	A
$I_{RRM}$		$T_j=150$	5	mA

## THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case(DC)	0.3	/W
$R_{th(j-a)}$	junction to ambient (DC)	60	/W



FIG.1: Maximum power dissipation versus  
RMS on-state current

FIG.2: RMS on-state current versus case  
temperature



ORDERING INFORMATION

Order Code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	1CID 1 6 /P	/M
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PACKAGE MECHANICAL DATA



